



Thermal resistance(Q1)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.1	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	° C/W

Soldering temperature, wavesoldering for 10s



(Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	2535	-	pF
Output capacitance	C_{oss}		-	196	-	
Reverse transfer capacitance	C_{rss}		-	139	-	

Gate Charge characteristics($T_a = 25$) (Q2)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	29	-	nC
Gate - Source charge	Q_{gs}	$I_D = 5A$	-	12	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	11	-	

Note: ① Pulse Test : ;



Channel characteristics curve(Q1)

Fig.1 Gate-Charge Characteristics

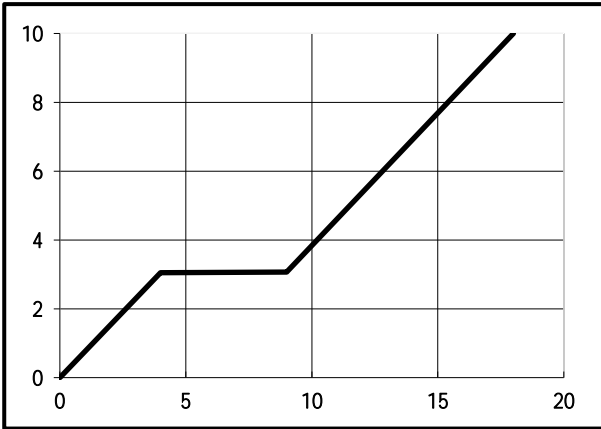


Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

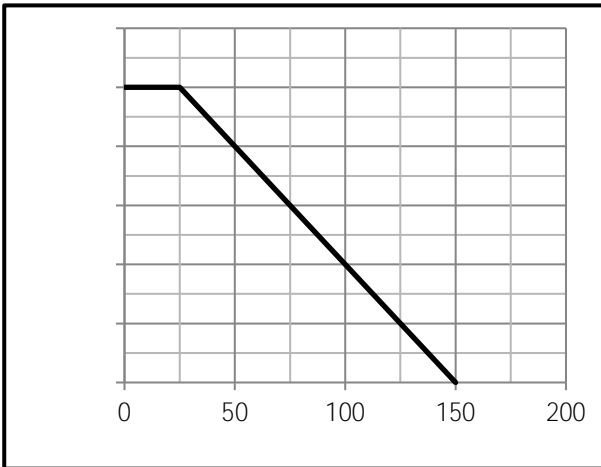


Fig.4 Typical output Characteristics

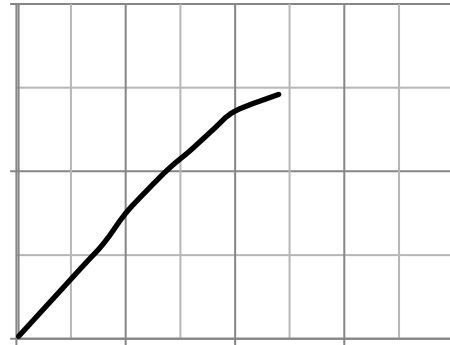
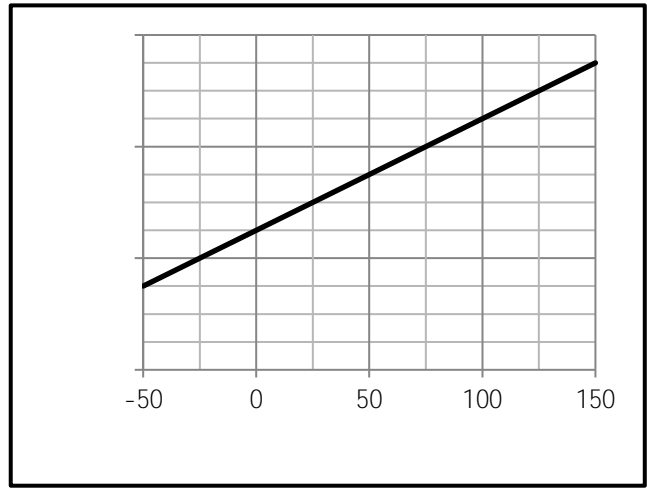
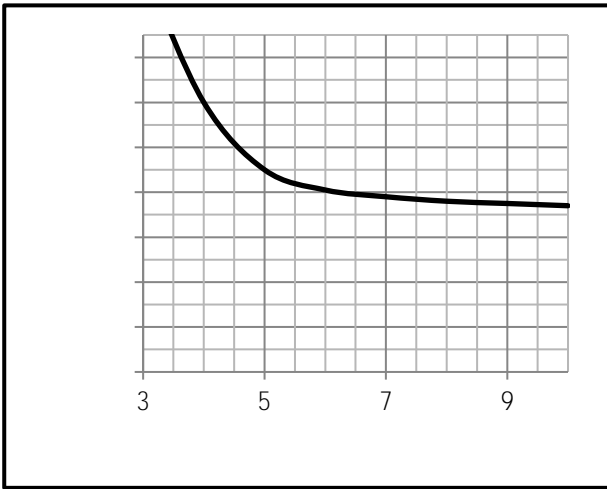


Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current



Channel characteristics curve(Q2)

Fig.9 Gate-Charge Characteristics

Fig.10 Capacitance Characteristics

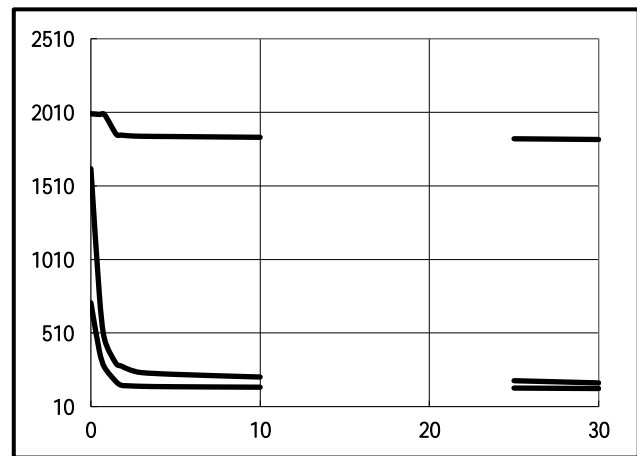
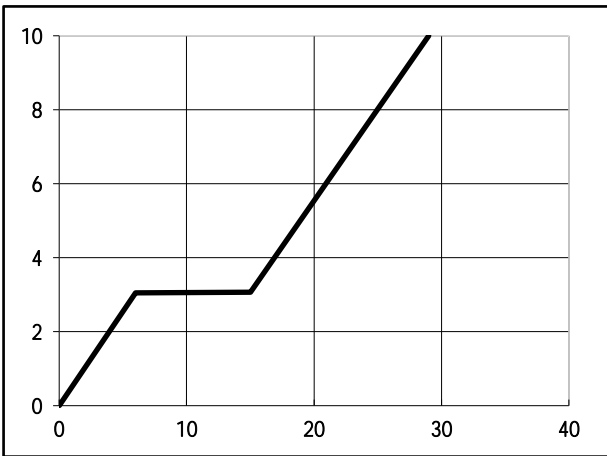


Fig.11 Power Dissipation

Fig.12 Typical output Characteristics

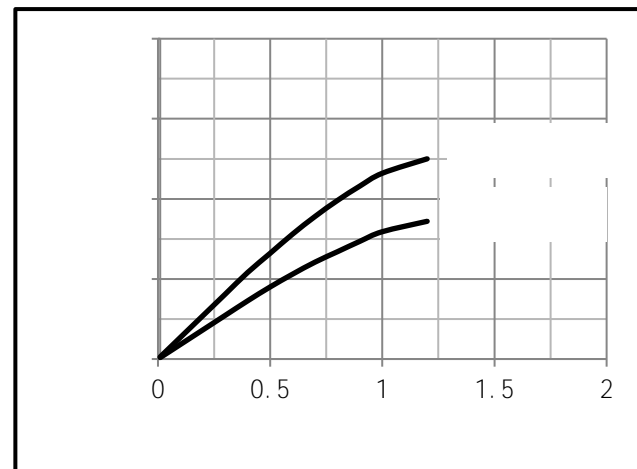
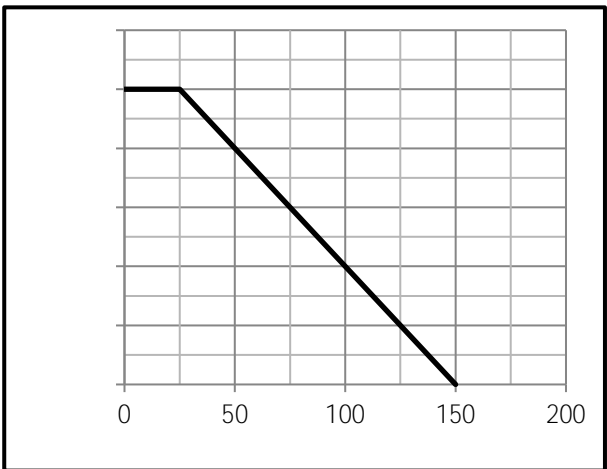
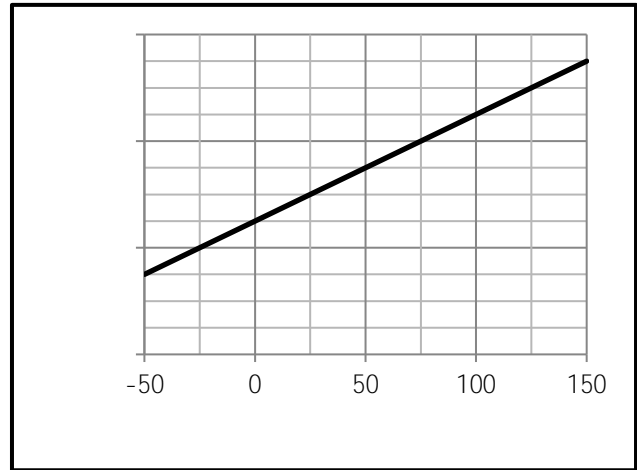
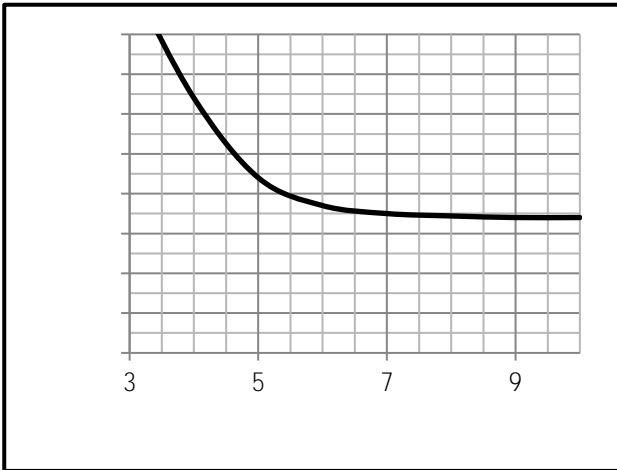
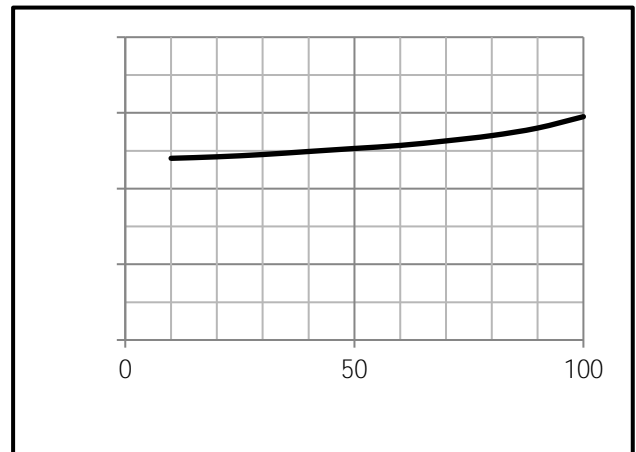
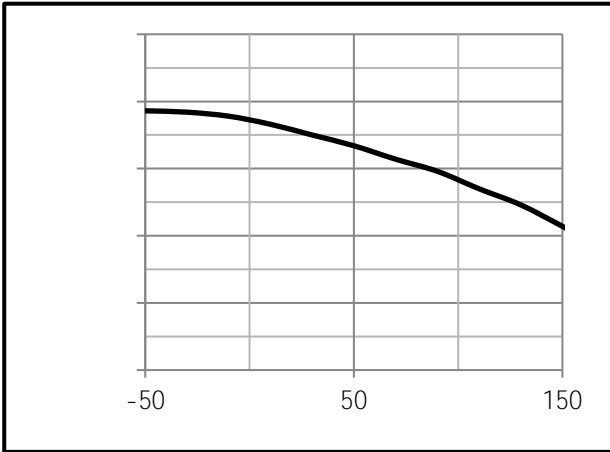




Fig.13 Threshold Voltage V.S Junction Temperature

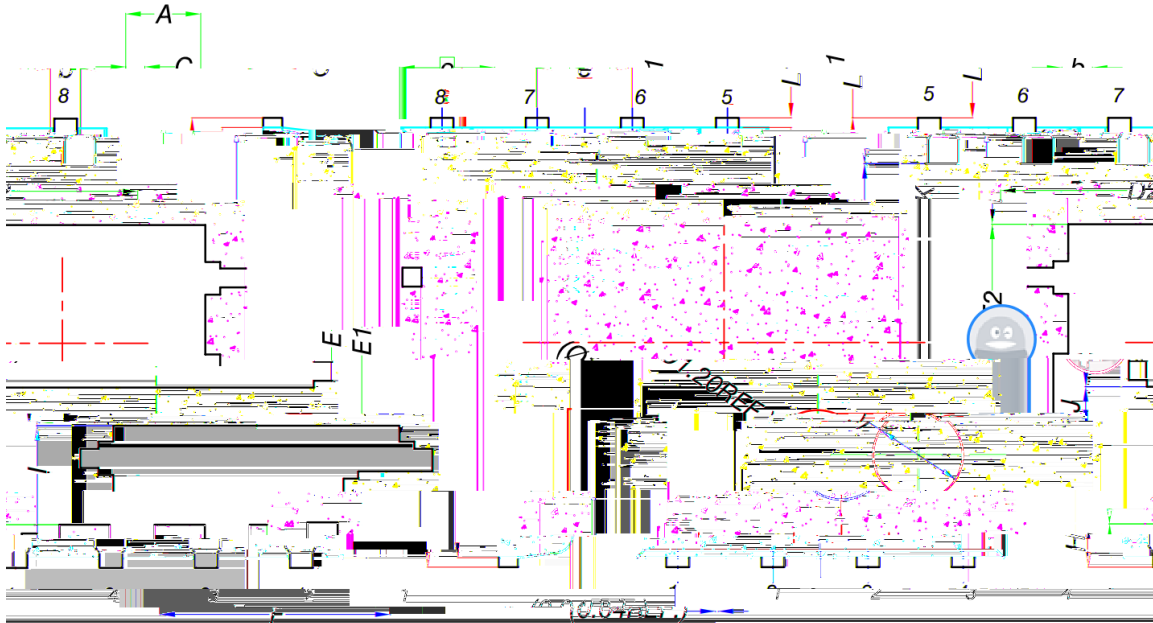
Fig.14 Resistance V.S Drain Current





sions DFN5x6

Unit mm



BACKSIDE VIEW

